

THAT WHICH IS CLAIMED:

1. A support fixture for holding at least one wafer comprising:
 - a boat comprised of a material selected from the group consisting of silicon carbide and graphite;
 - a first layer on at least a portion of said boat and comprised of silicon carbide; and
 - a second layer on at least a portion of said first layer and comprised of polysilicon.
2. A support fixture according to Claim 1 wherein said first layer has a greater purity than said boat.
3. A support fixture according to Claim 1 wherein said second layer has a hardness that more closely matches a hardness of the at least one wafer than a hardness of said boat.
4. A support fixture according to Claim 1 wherein said second layer has a coefficient of thermal expansion that more closely matches a coefficient of thermal expansion of the at least one wafer than a coefficient of thermal expansion of said boat.
5. A support fixture according to Claim 1 wherein said first layer completely surrounds said boat.
6. A support fixture according to Claim 1 wherein said first and second layers are chemical vapor deposition layers.
7. A support fixture for holding at least one wafer comprising:
 - a boat;
 - a first layer on at least a portion of said boat, wherein said first layer has a greater purity than said boat; and
 - a second layer on at least a portion of said first layer, wherein said second layer is formed of a different material than said first layer and said boat, and wherein said second layer has at least one material property selected from the group consisting of: (i) a

hardness that more closely matches a hardness of the at least one wafer than a hardness of said boat, and (ii) a coefficient of thermal expansion that more closely matches a coefficient of thermal expansion of the at least one wafer than a coefficient of thermal expansion of said boat.

8. A support fixture according to Claim 7 wherein said first layer and said boat are comprised of silicon carbide.

9. A support fixture according to Claim 7 wherein said second layer is comprised of polysilicon.

10. A support fixture according to Claim 7 wherein said first layer completely surrounds said boat.

11. A support fixture according to Claim 7 wherein said first and second layers are chemical vapor deposition layers.

12. A method of fabricating a support fixture for holding at least one wafer comprising:

providing a boat comprised of a material selected from the group consisting of silicon carbide and graphite;

depositing a first layer of silicon carbide on at least a portion of said boat; and
depositing a second layer of polysilicon on at least a portion of the first layer.

13. A method according to Claim 12 wherein depositing the first layer comprises depositing the first layer so as to completely surround the boat.

14. A method according to Claim 12 wherein depositing the first layer comprises depositing the first layer via chemical vapor deposition.

15. A method according to Claim 12 wherein depositing the second layer comprises depositing the second layer via chemical vapor deposition.

16. A method of fabricating a support fixture for holding at least one wafer comprising:

depositing a first layer on at least a portion of a boat, wherein depositing the first layer comprises depositing a first layer that has a greater purity than the boat; and

depositing a second layer on at least a portion of the first layer, wherein depositing the second layer comprises depositing a second layer that is formed of a different material than the first layer and the boat and that has at least one material property selected from the group consisting of: (i) a hardness that more closely matches a hardness of the at least one wafer than a hardness of the boat, and (ii) a coefficient of thermal expansion that more closely matches a coefficient of thermal expansion of the at least one wafer than a coefficient of thermal expansion of the boat.

17. A method according to Claim 16 wherein the boat is comprised of silicon carbide, and wherein depositing the first layer comprises depositing a first layer comprised of silicon carbide.

18. A method according to Claim 16 wherein depositing the second layer comprises depositing a second layer comprised of polysilicon.

19. A method according to Claim 16 wherein depositing the first layer comprises depositing the first layer so as to completely surround the boat.

20. A method according to Claim 16 wherein depositing the first layer comprises depositing the first layer via chemical vapor deposition.

21. A method according to Claim 16 wherein depositing the second layer comprises depositing the second layer via chemical vapor deposition.